

66183	PROTON RADIATION TOLERANT OPTOCOUPLER (Single Channel, Electrically Similar to 4N49)	Mii OPTOELECTRONIC PRODUCTS DIVISION
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REVISION C 5/6/02

<p>Features:</p> <ul style="list-style-type: none"> • High Reliability • Base lead provided for conventional transistor biasing • Rugged package • Stability over wide temperature • +1000V electrical isolation 	<p>Applications:</p> <ul style="list-style-type: none"> • Eliminate ground loops • Level shifting • Line receiver • Switching power supplies • Motor control
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DESCRIPTION

The **66183** is a single channel device electrically similar to the 4N49. This product has been designed to be more tolerant to proton radiation. The 66183 optocoupler is packaged in a hermetically sealed 6 pin leadless chip carrier (LCC). This device can be supplied to customer specifications as well as tested in accordance with MIL-PRF-19500 to Class S level.

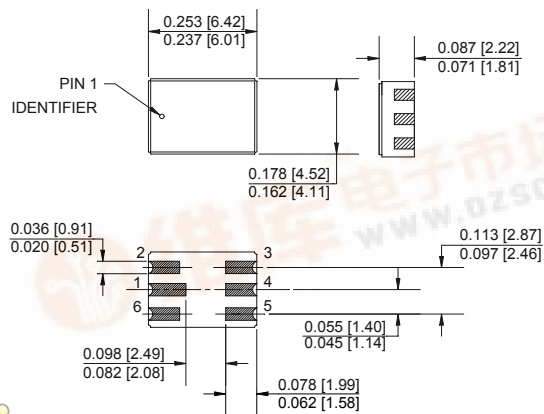
ABSOLUTE MAXIMUM RATINGS

Input to Output Voltage	1kV
Emitter-Base Voltage	7V
Collector-Emitter Voltage (Value applies to emitter-base open-circuited & the input-diode equal to zero)	40V
Collector-Base Voltage	45V
Reverse Input Voltage	2V
Input Diode Continuous Forward Current at (or below) 65°C Free-Air Temperature (see note 1)	50mA
Peak Forward Input Current (Value applies for $t_w \leq 1\mu s$, PRR < 300 pps)	1A
Continuous Collector Current	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 2)	300mW
Storage Temperature	-55°C to +150°C
Operating Free-Air Temperature Range	-55°C to +100°C
Lead Solder Temperature (10 seconds max.)	240°C

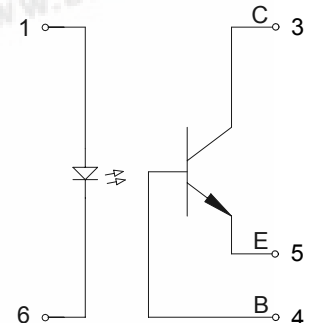
Notes:

1. Derate linearly to 100°C free-air temperature at the rate of 0.80 mW/°C above 25°C.
2. Derate linearly to 100°C free-air temperature at the rate of 3 mW/°C above 25°C.

Package Dimensions



Schematic Diagram



ALL DIMENSIONS ARE IN INCHES [MILLIMETERS]

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ELECTRICAL CHARACTERISTICS

T_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Input Diode Static Reverse Current	I _R			100	μA	V _R = 3V	
Input Diode Static Forward Voltage -55°C	V _F	1.0		2.2	V	I _F = 10mA	
Input Diode Static Forward Voltage +25°C	V _F	0.8	1.8	2.0	V	I _F = 10mA	
Input Diode Static Forward Voltage +100°C	V _F	0.8		2.2	V	I _F = 10mA	

OUTPUT TRANSISTOR

T_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	V _{(BR)CBO}	45			V	I _C = 100μA, I _B = 0, I _F = 0	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40			V	I _C = 1mA, I _B = 0, I _F = 0	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	2			V	I _C = 0mA, I _E = 100μA, I _F = 0	
Off-State Collector Current	I _{CEO}			100	nA	V _{CE} = 20V, I _F = 0mA, I _B = 0	
+100°C	I _{CEO}			100	μA	V _{CE} = 20V, I _F = 0mA, I _B = 0	

COUPLED CHARACTERISTICS

T_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
On State Collector Current	I _{C(ON)}	2.0			mA	V _{CE} = 5V, I _F = 1mA, I _B = 0	
On State Collector Current +100°C	I _{C(ON)}	2.0			mA	V _{CE} = 5.0V, I _F = 2mA, I _B = 0	
On State Collector Current -55°C	I _{C(ON)}	2.8			mA	V _{CE} = 5V, I _F = 2mA, I _B = 0	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.3	V	I _F = 2mA, I _C = 2mA	
Input to Output Internal Resistance	R _{IO}	10 ¹¹			Ω	V _{IN-OUT} = 1000V	1
Input to Output Capacitance	C _{IO}		2.5	5	pF	f = 1MHz, V _{IN-OUT} = 1000V	1
Rise Time-Phototransistor Operation	t _r		10	25	μs	V _{CC} = 10V, I _F = 10mA, R _L = 100Ω, I _B = 0	
Fall Time-Phototransistor Operation	t _f		10	25	μs	V _{CC} = 10V, I _F = 10mA, R _L = 100Ω, I _B = 0	

NOTES:

- These parameters are measured between all phototransistor leads shorted together and with both input diode leads shorted together.
- This parameter must be measured using pulse techniques (t_W = 100μs duty cycle ≤ 1%).

RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	I _{FL}	0	90	μA
Input Current, High Level	I _{FH}	2	10	mA
Supply Voltage	V _{CE}	5	10	V
Operating Temperature	T _A	-55	100	°C

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION
66183-001	Single channel proton radiation tolerant optocoupler - commercial
66183-101	Single channel proton radiation tolerant optocoupler - screened to JAN
66183-103	Single channel proton radiation tolerant optocoupler - screened to JANTX
66183-105	Single channel proton radiation tolerant optocoupler - screened to JANTXV